

0039-7684-2SRD



RESPONSE UNDER 37 CFR 1.116 -
EXPEDITED PROCEDURE EXAMINING
GROUP 2823

RECEIVED

AUG 13 2001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE MAIL ROOM

IN RE APPLICATION OF: :
Hisako AOYAMA, et al. : GROUP ART UNIT: 2823
SERIAL NO.: 09/558,053 :
FILED: April 26, 2000 : EXAMINER: EATON, K.
FOR: SEMICONDUCTOR DEVICE... :

#10/D
8/14/01
V. Vannal

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office Action dated April 9, 2001, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel claims 28 and 41 without prejudice.

Please amend claims 29 and 40 as provided in the marked-up copy to read as follows:

29. (Amended) A process of fabricating a semiconductor device comprising the steps of:

forming a first insulating film on a semiconductor substrate;

forming a second insulating film on said first insulating film, said second insulating film

being made of a material different from that of the first insulating film and having a thickness smaller than that of the first insulating film;

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